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Okuyama et al.

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(54) **SEMICONDUCTOR ELEMENT**

(75) Inventors: **Hiroyuki Okuyama**, Tokyo (JP); **Masato Doi**, Tokyo (JP); **Goshi Biwa**, Tokyo (JP); **Toyoharu Oohata**, Tokyo (JP)

(73) Assignee: **Sony Corporation**, Tokyo (JP)

(**) Term: **14 Years**

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(51) **LOC (7) Cl.** **13-03**

(52) **U.S. Cl.** **D13/182**

(58) **Field of Search** D13/182; D14/172, D14/212, 233; 117/95; 216/227; 257/146, 618; 313/309, 310, 327, 336; 369/112.08, 112.09; 438/460

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Primary Examiner—Ted Shooman

(74) *Attorney, Agent, or Firm*—Rader, Fishman & Grauer PLLC

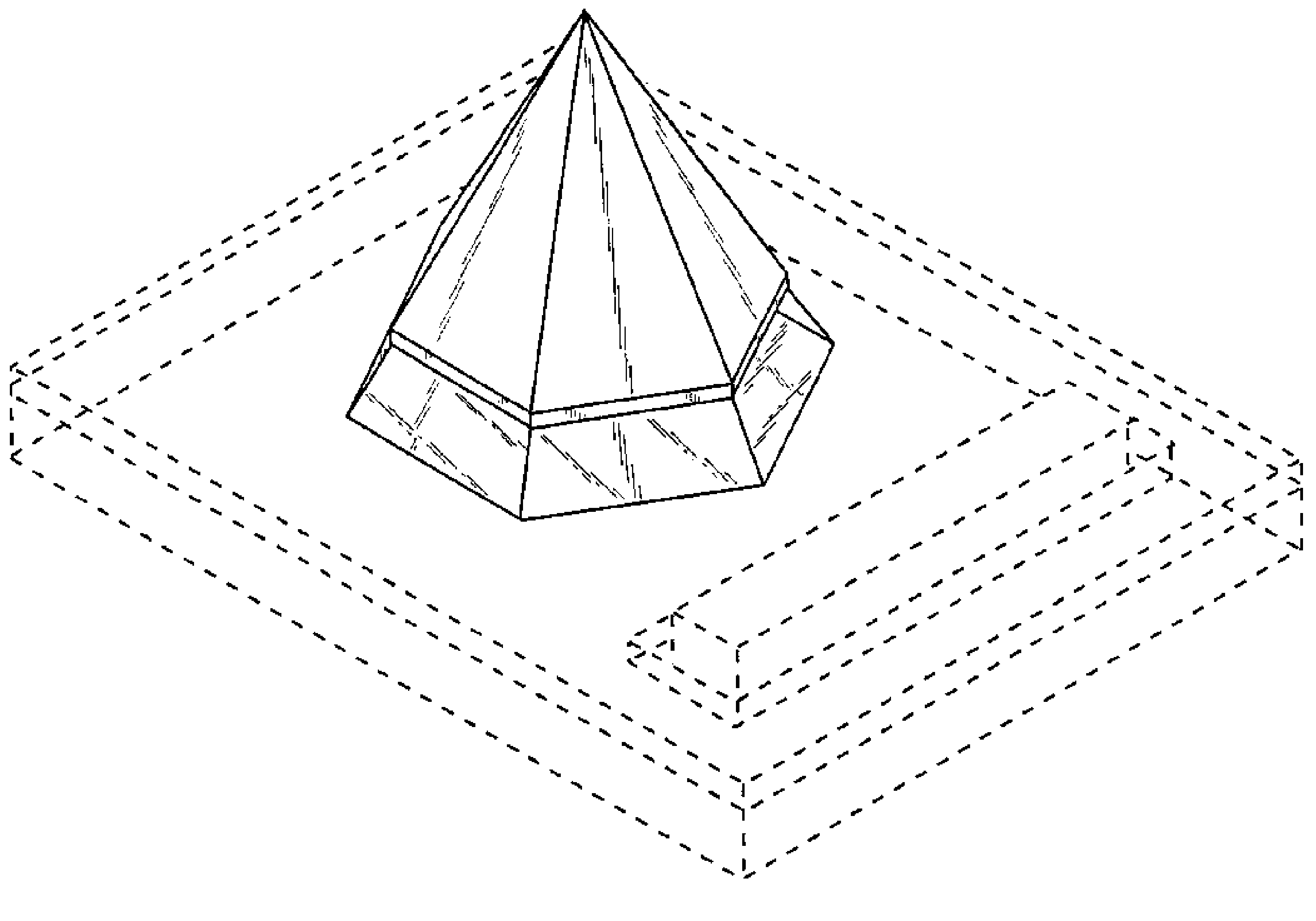
(57) CLAIM

The ornamental design for a semiconductor element, as shown and described.

DESCRIPTION

FIG. **1** is front perspective of a semiconductor element showing our new design, wherein the truncated hexagonal pyramid portion thereof is transparent;
FIG. **2** is a front elevational view thereof;
FIG. **3** is a rear elevational view thereof;
FIG. **4** is a right side elevational view thereof;
FIG. **5** is a left side elevational view thereof; and,
FIG. **6** is a top plan view thereof.
Portions in broken lines are for illustrative purposes only and form no part of claimed design.

1 Claim, 4 Drawing Sheets



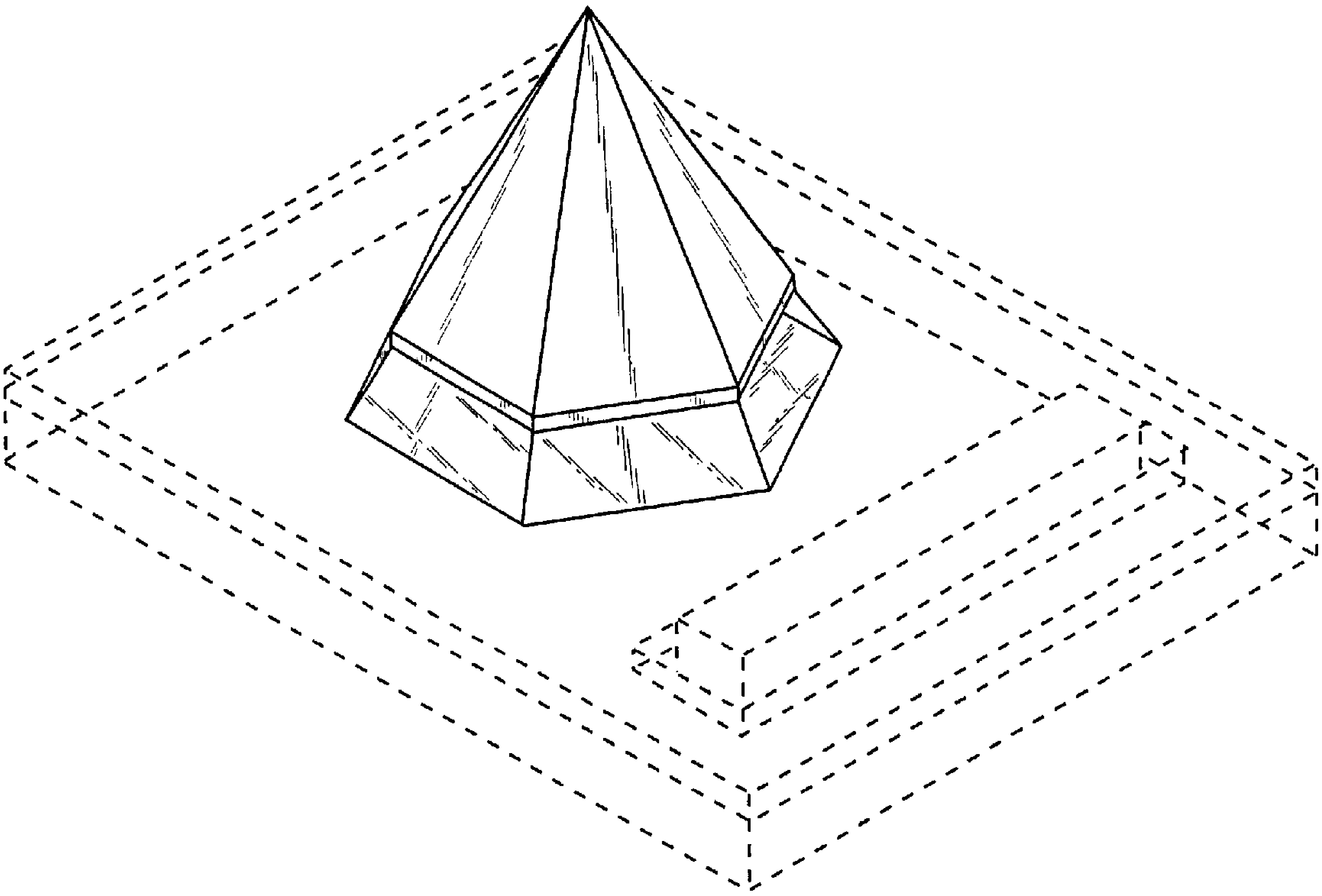


Fig. 1

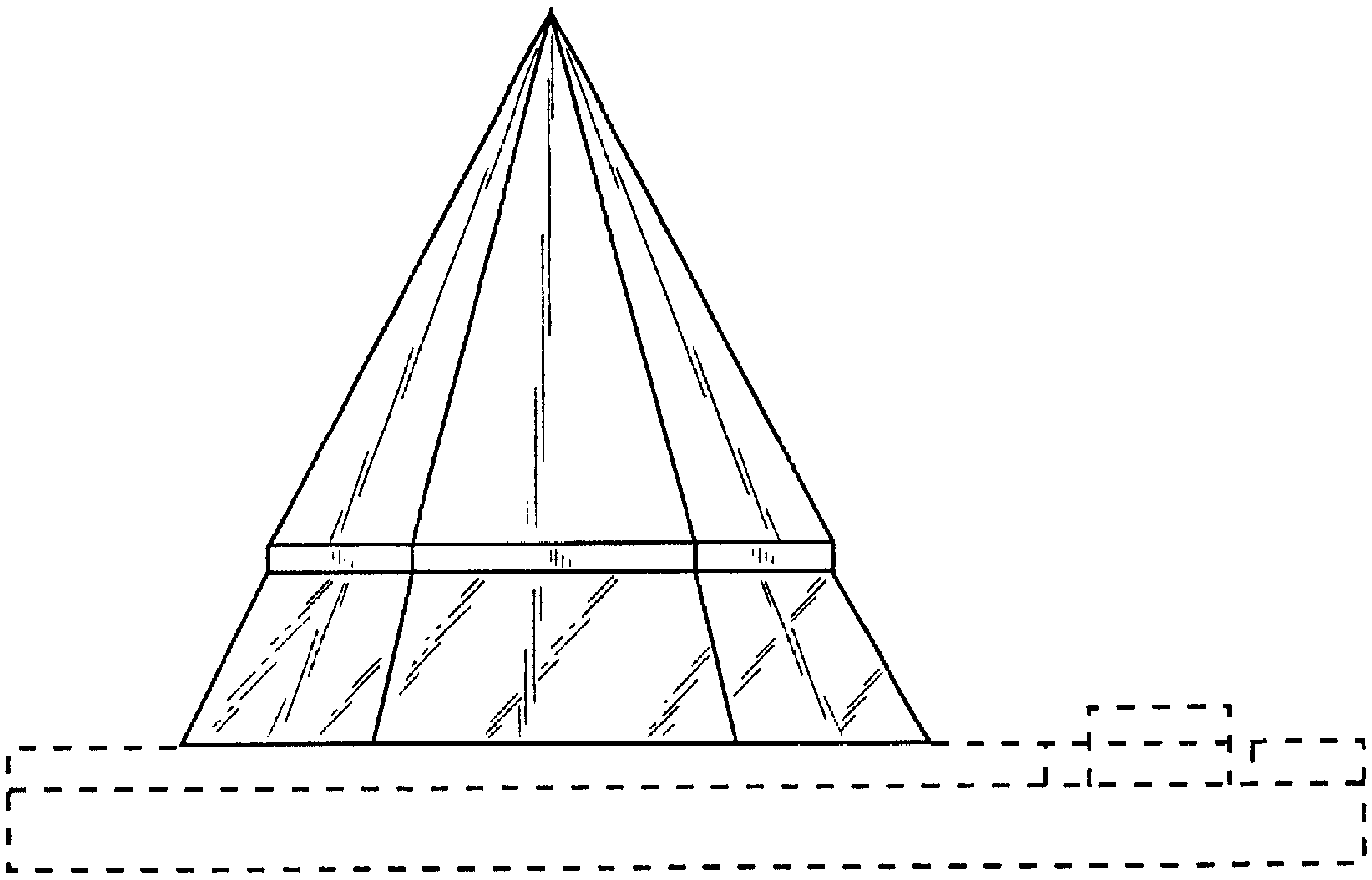


Fig. 2

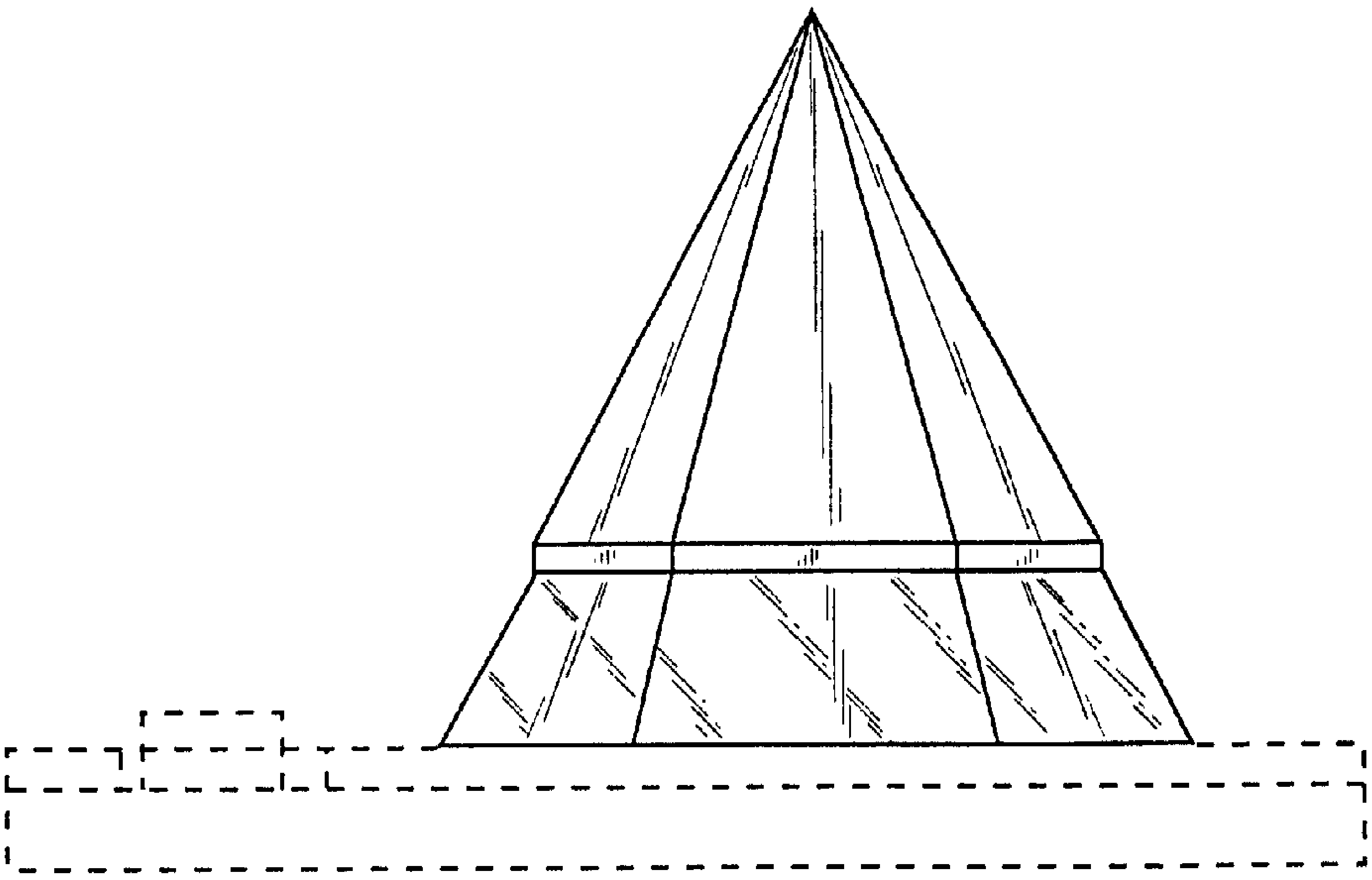


Fig. 3

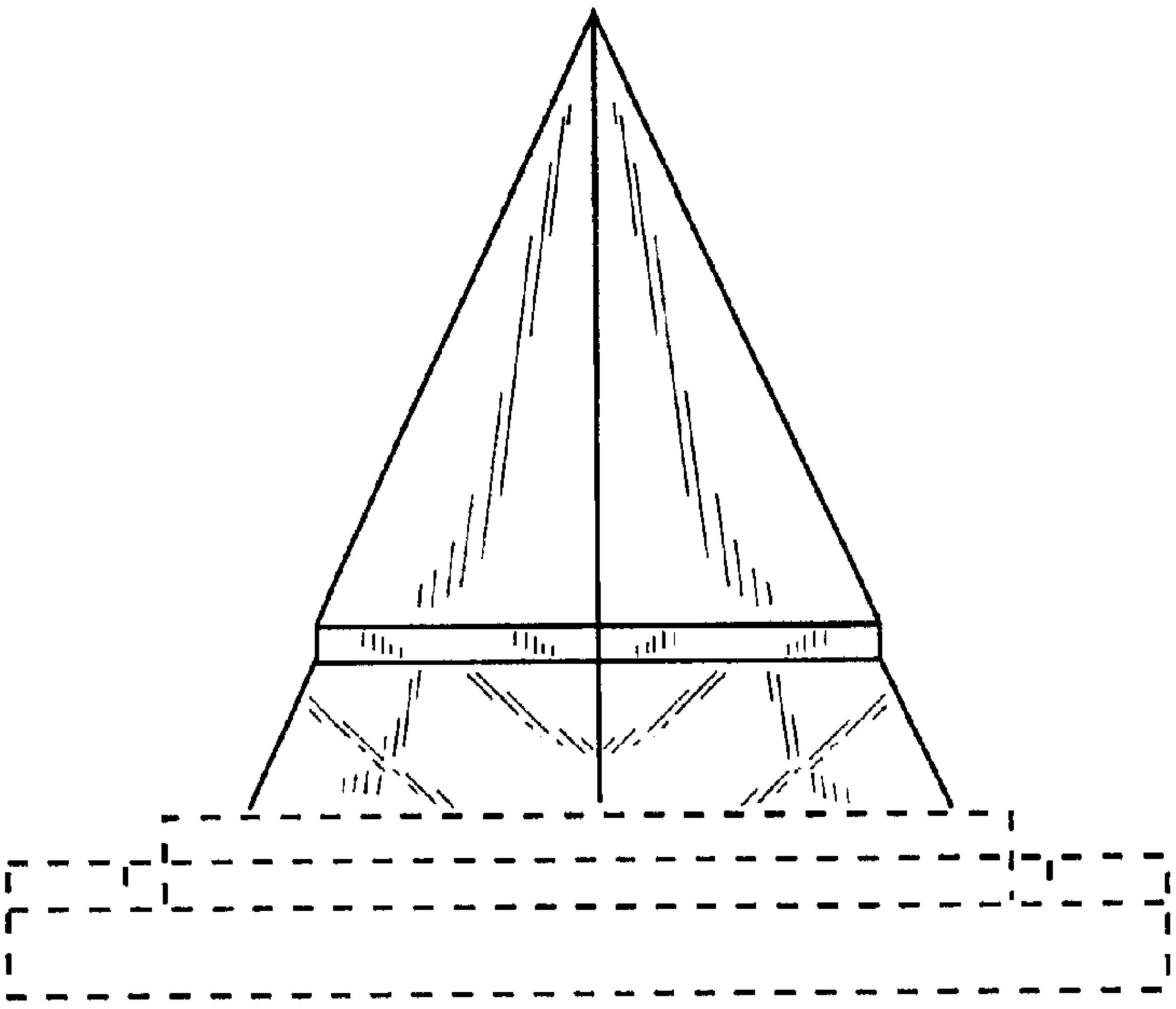


Fig. 4

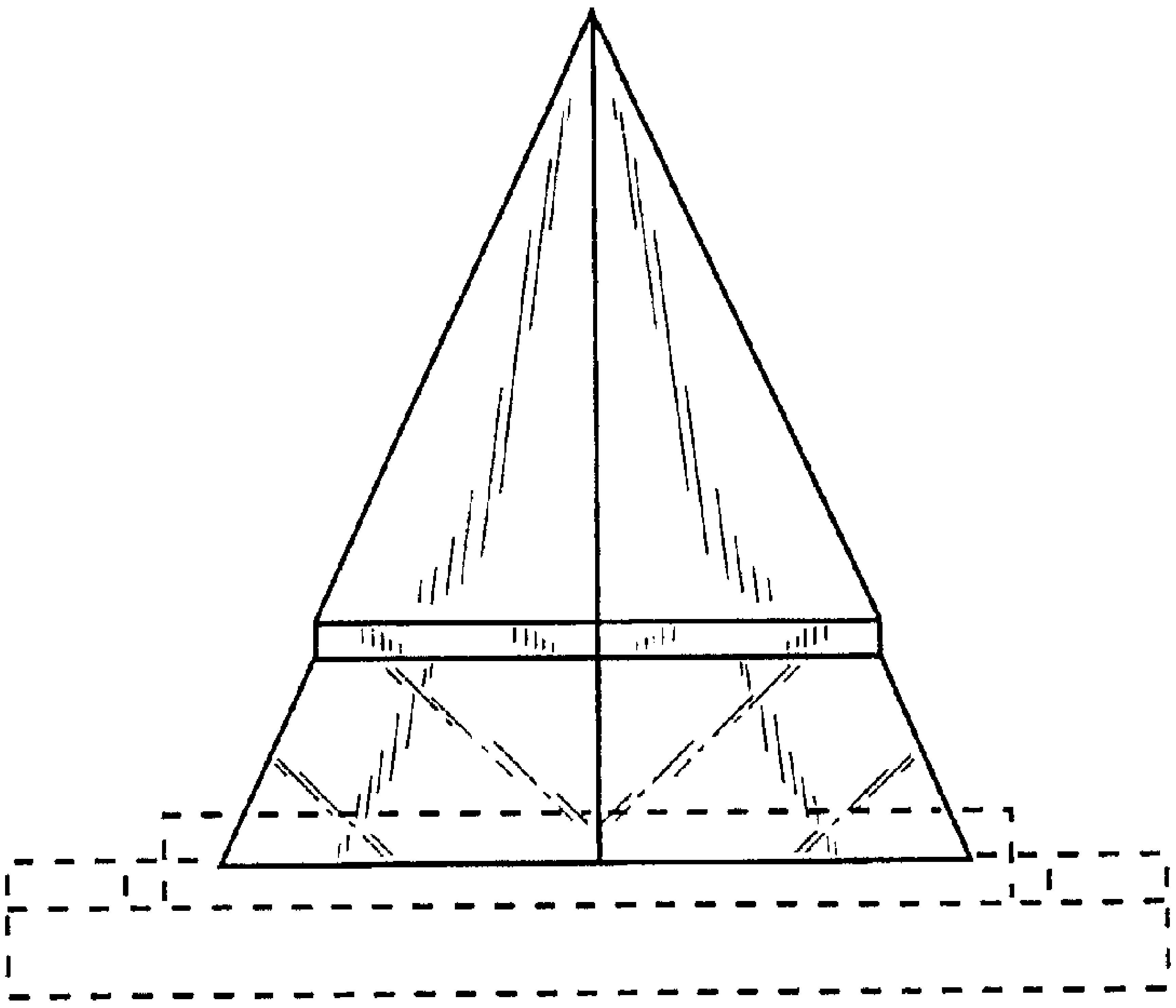


Fig. 5

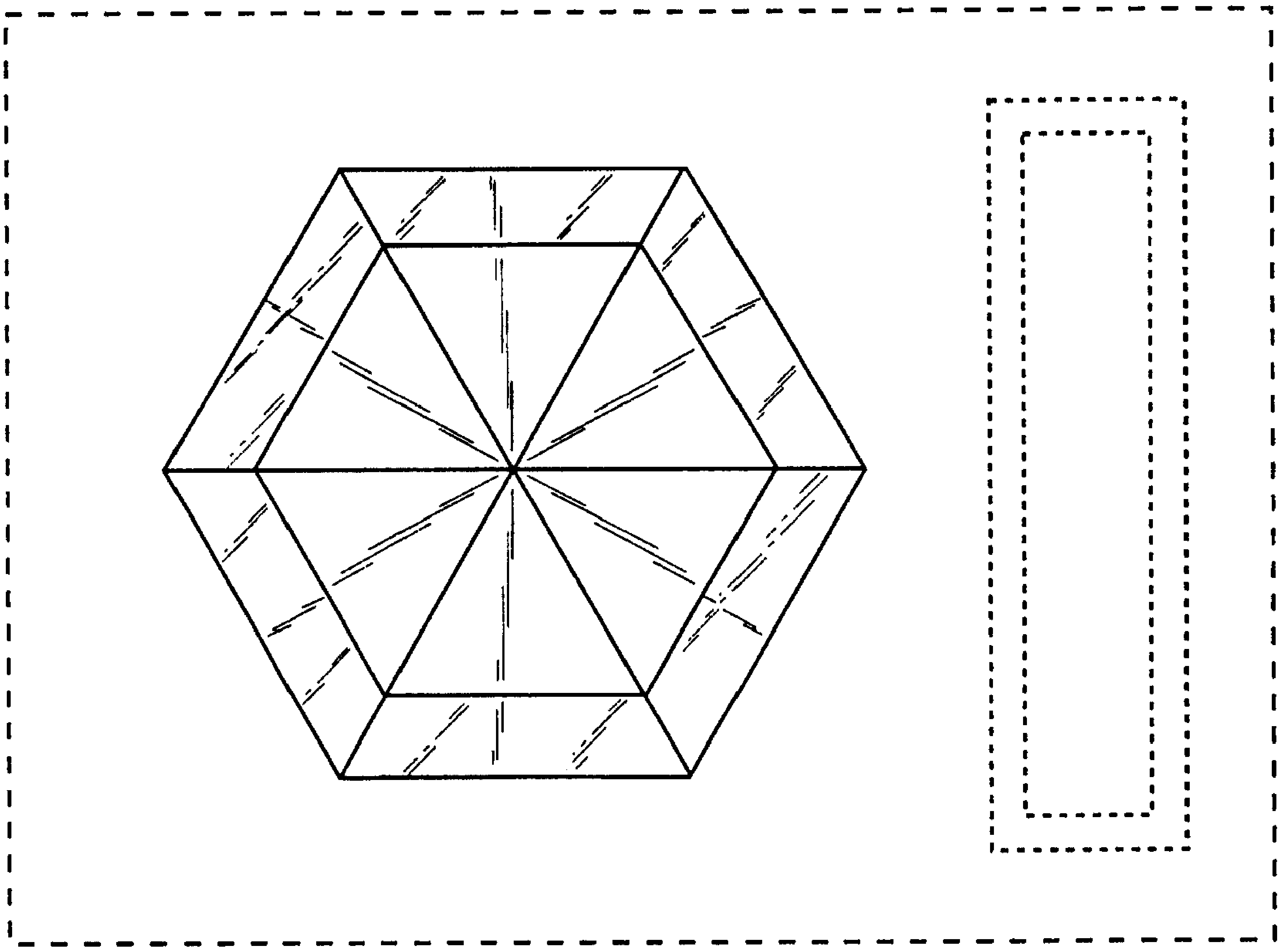


Fig. 6